

CMSA100P02-VB Datasheet

P-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY

V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A) ^a	Q_g (Typ.)
- 30	0.004 at $V_{GS} = - 10$ V	- 120	130 nC
	0.006 at $V_{GS} = - 4.5$ V	- 100	

FEATURES

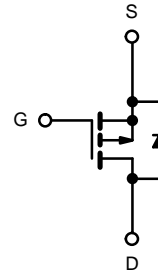
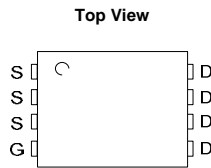
- Halogen-free
- Trench Power MOSFET
- 100 % R_g Tested



RoHS
COMPLIANT

APPLICATIONS

- Notebook
- Load Switch



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	- 30	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ($T_J = 150$ °C)	I_D	$T_C = 25$ °C	A
		$T_C = 70$ °C	
		$T_A = 25$ °C	
		$T_A = 70$ °C	
Pulsed Drain Current	I_{DM}	- 280	mJ
Continuous Source-Drain Diode Current	I_S	$T_C = 25$ °C	
		$T_A = 25$ °C	
Single Pulse Avalanche Current	I_{AS}	- 60	
Single Pulse Avalanche Energy	E_{AS}	160	
Maximum Power Dissipation	P_D	$T_C = 25$ °C	W
		$T_C = 70$ °C	
		$T_A = 25$ °C	
		$T_A = 70$ °C	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150	°C
Soldering Recommendations (Peak Temperature) ^{d, e}		260	

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^{b, f}	R_{thJA}	15	20	°C/W
Maximum Junction-to-Case (Drain)	R_{thJC}	0.9	1.2	

Notes:

a. Package limited.

b. Surface Mounted on 1" x 1" FR4 board.

c. $t = 10$ s.

d. The DFN5x6 is a leadless package. The end of the lead terminal is exposed

copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

e. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.

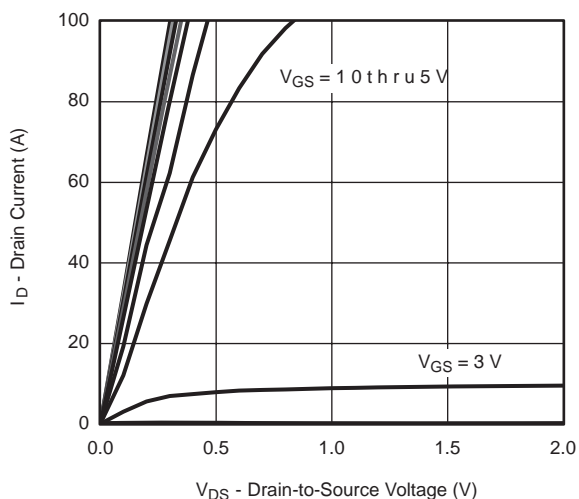
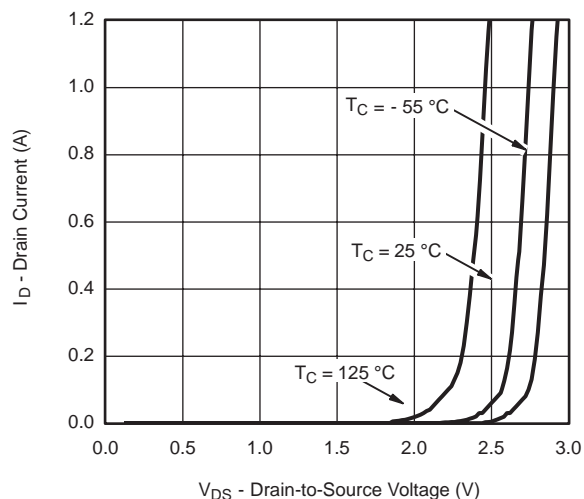
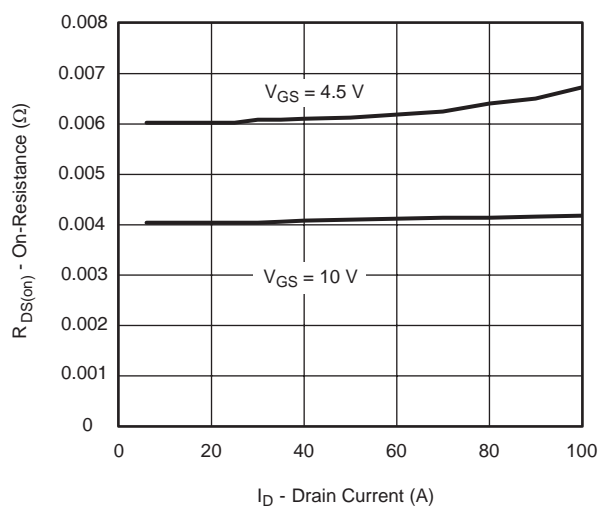
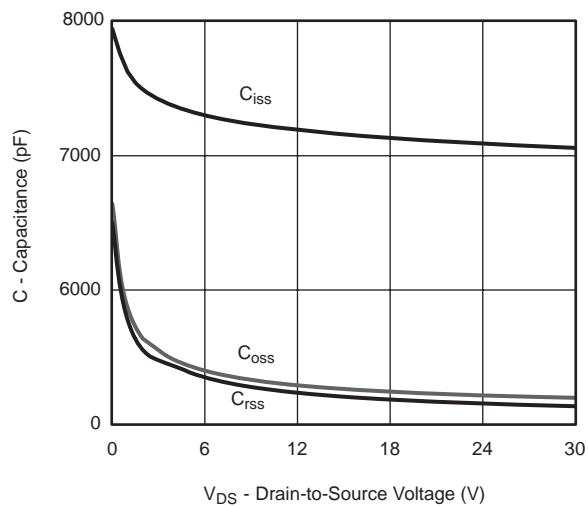
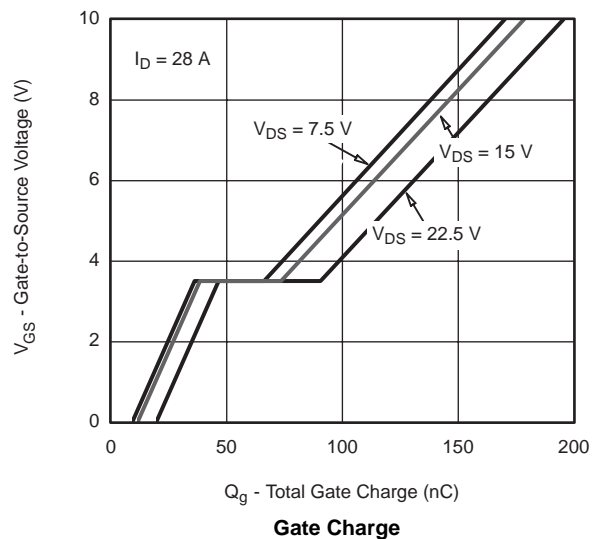
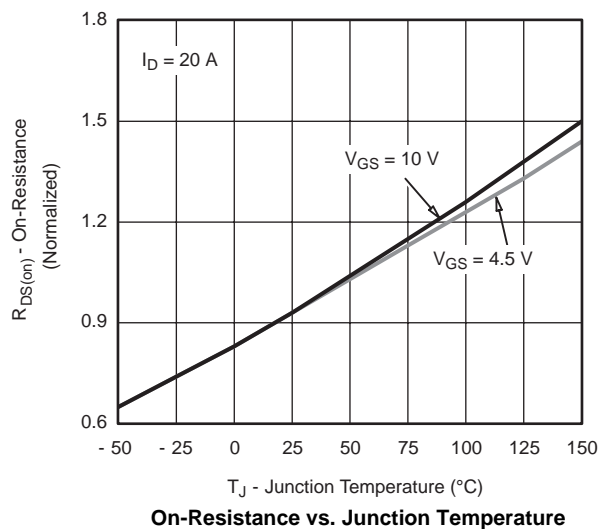
f. Maximum under Steady State conditions is 54 °C/W.

SPECIFICATIONS $T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$	- 30			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = -250\text{ }\mu\text{A}$		- 31		mV/ $^{\circ}\text{C}$
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			6.5		
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	- 1.0		- 3.0	V
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -30\text{ V}, V_{GS} = 0\text{ V}$			- 1	μA
		$V_{DS} = -30\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^{\circ}\text{C}$			- 10	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} = -5\text{ V}, V_{GS} = -10\text{ V}$	- 30			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = -10\text{ V}, I_D = -20\text{ A}$		0.004		Ω
		$V_{GS} = -4.5\text{ V}, I_D = -15\text{ A}$		0.006		
Forward Transconductance ^a	g_{fs}	$V_{DS} = -15\text{ V}, I_D = -20\text{ A}$		97		S
Dynamic ^b						
Input Capacitance	C_{iss}	$V_{DS} = -15\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		7050		pF
Output Capacitance	C_{oss}			1375		
Reverse Transfer Capacitance	C_{rss}			1215		
Total Gate Charge	Q_g	$V_{DS} = -15\text{ V}, V_{GS} = -10\text{ V}, I_D = -20\text{ A}$		130	250	nC
				78	130	
Gate-Source Charge	Q_{gs}	$V_{DS} = -15\text{ V}, V_{GS} = -4.5\text{ V}, I_D = -20\text{ A}$		29		
Gate-Drain Charge	Q_{gd}			37		
Gate Resistance	R_g	$f = 1\text{ MHz}$		1.9		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -15\text{ V}, R_L = 15\text{ }\Omega$ $I_D \cong -1.0\text{ A}, V_{GEN} = -10\text{ V}, R_g = 1\text{ }\Omega$		25	40	ns
Rise Time	t_r			15	30	
Turn-Off Delay Time	$t_{d(off)}$			110	170	
Fall Time	t_f			30	50	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -15\text{ V}, R_L = 15\text{ }\Omega$ $I_D \cong -1.0\text{ A}, V_{GEN} = -4.5\text{ V}, R_g = 1\text{ }\Omega$		110	170	
Rise Time	t_r			100	150	
Turn-Off Delay Time	$t_{d(off)}$			100	150	
Fall Time	t_f			50	75	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	$T_C = 25\text{ }^{\circ}\text{C}$			100	A
Pulse Diode Forward Current ^a	I_{SM}				120	
Body Diode Voltage	V_{SD}	$I_S = -5\text{ A}$		- 0.54	- 1.1	V
Body Diode Reverse Recovery Time	t_{rr}	$I_F = 3.5\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^{\circ}\text{C}$		50	100	ns
Body Diode Reverse Recovery Charge	Q_{rr}			65	130	nC
Reverse Recovery Fall Time	t_a			26		ns
Reverse Recovery Rise Time	t_b			24		

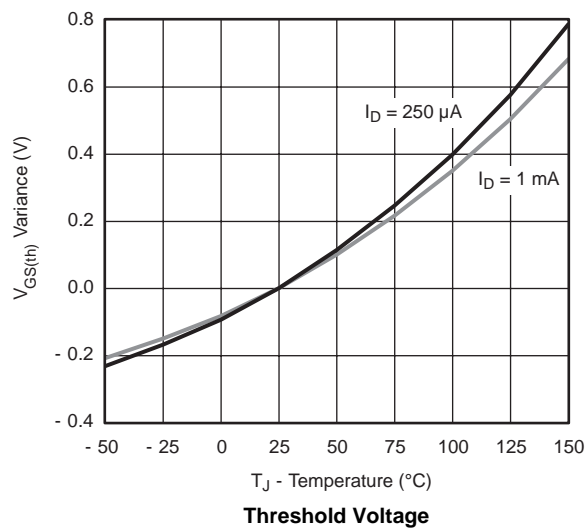
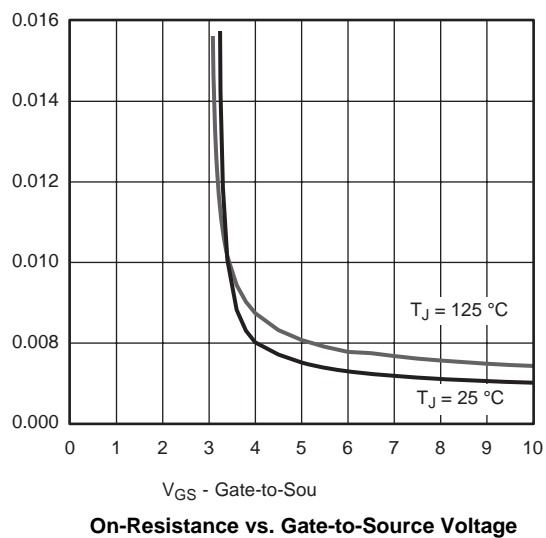
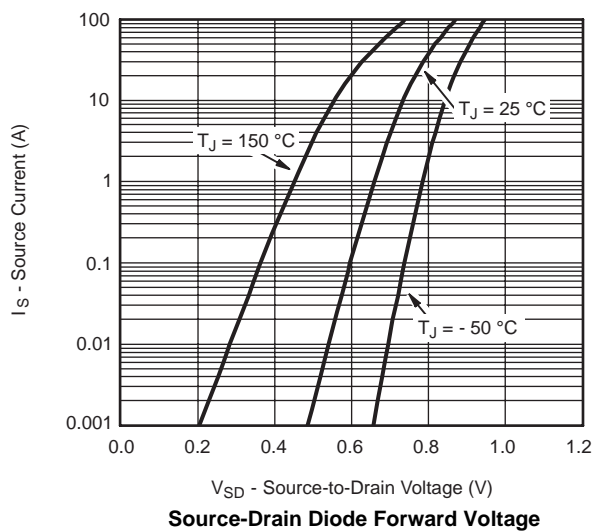
Notes:

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
 b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

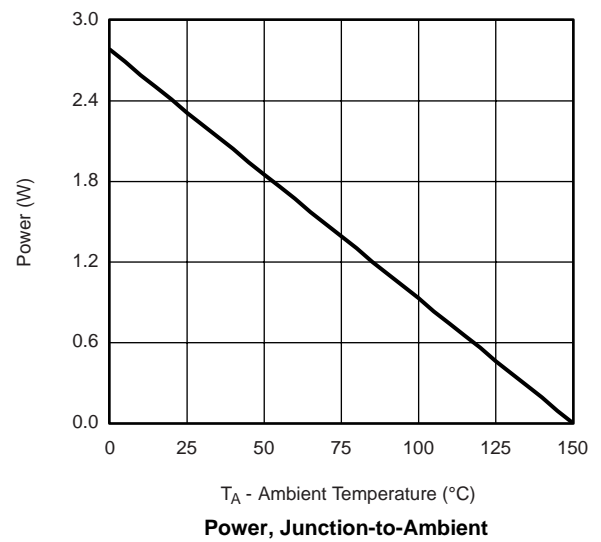
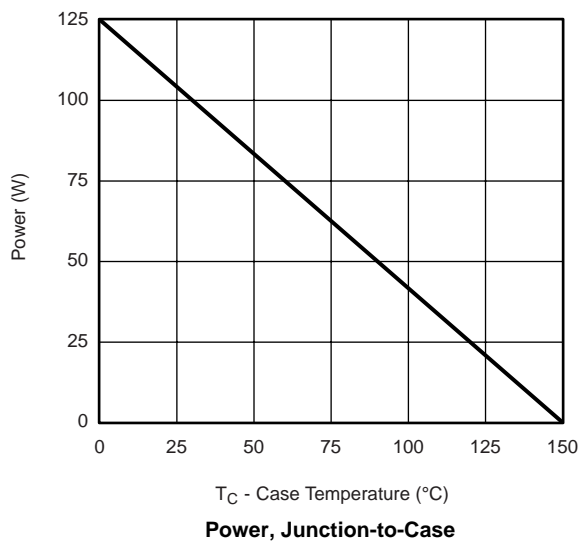
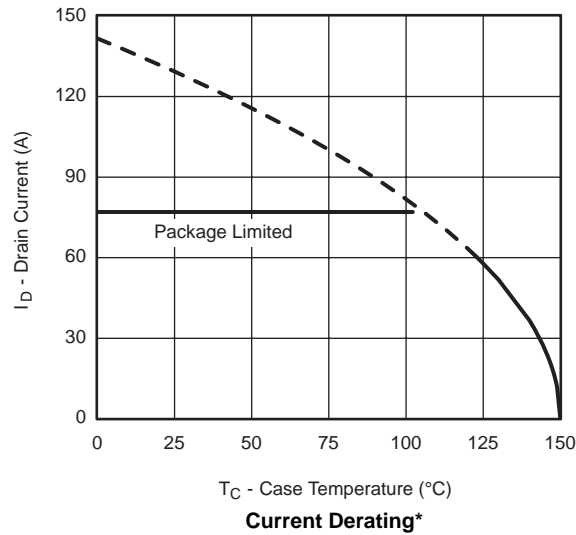
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

Output Characteristics

Transfer Characteristics

On-Resistance vs. Drain Current and Gate Voltage

Capacitance

Gate Charge

On-Resistance vs. Junction Temperature

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



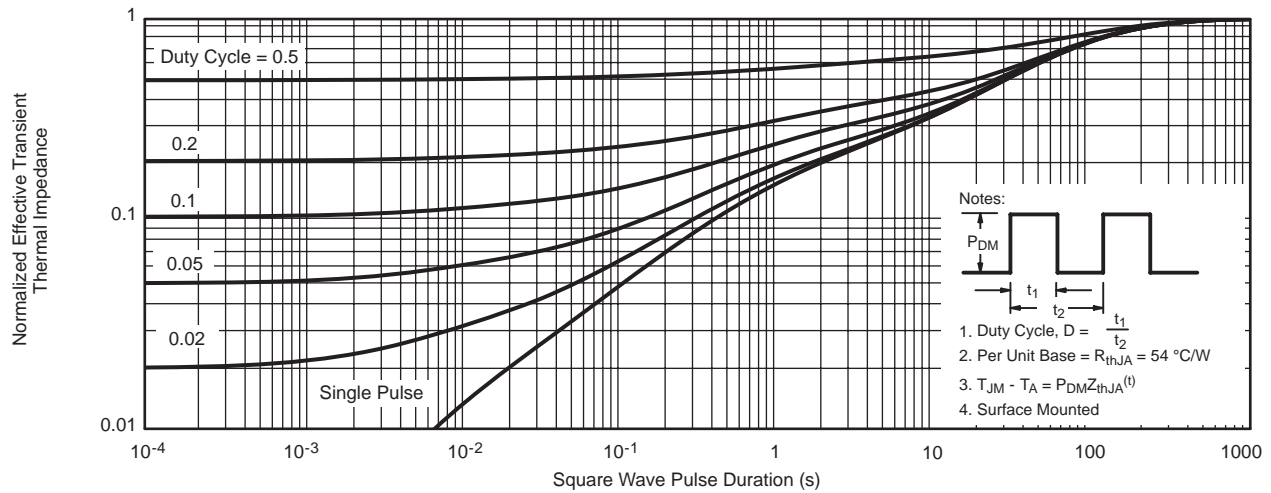
Single Pulse Power, Junction-to-Ambient

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

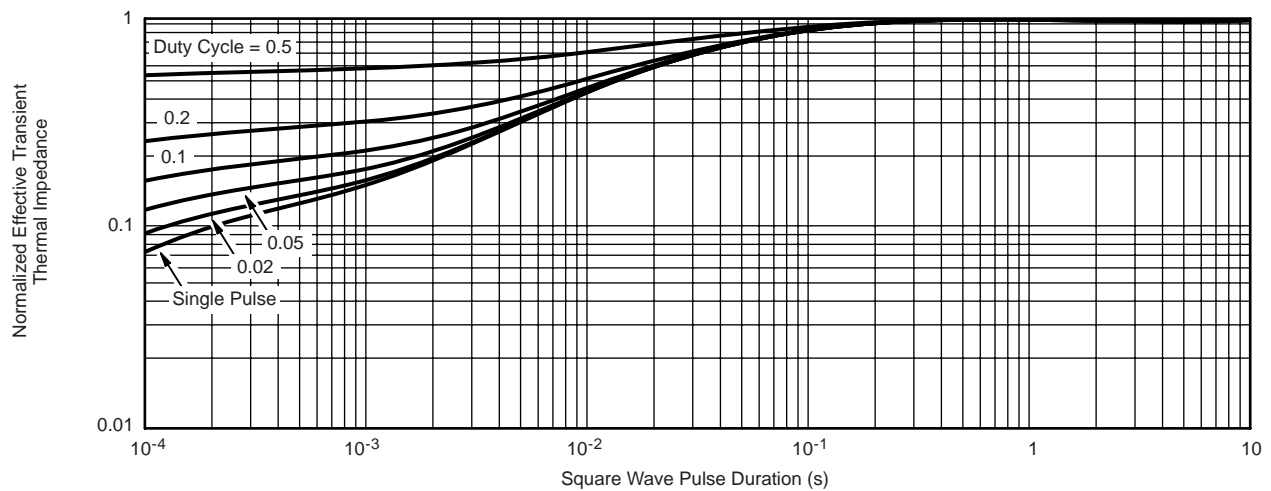


* The power dissipation P_D is based on $T_{J(max)} = 150\text{ °C}$, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

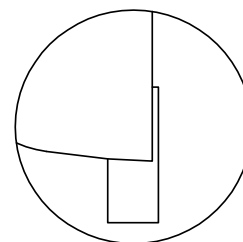
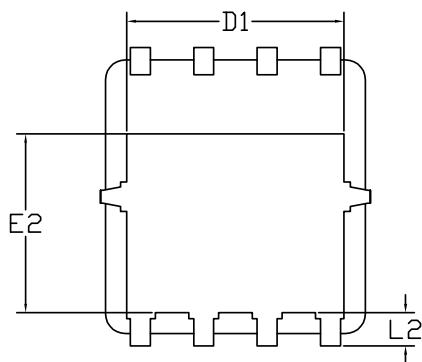
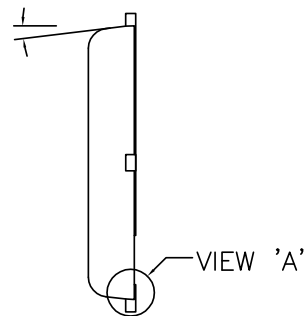
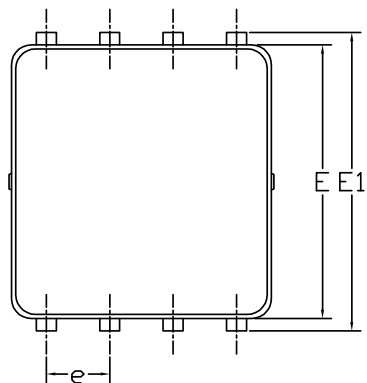
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



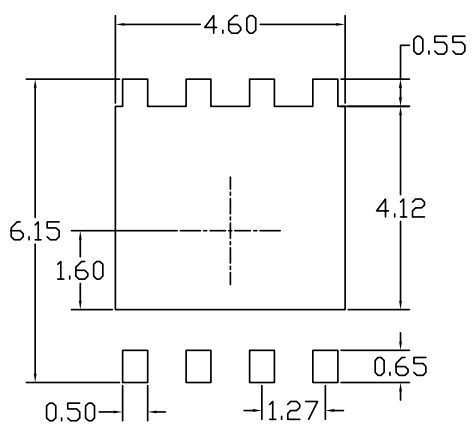
Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case



VIEW 'A'
(SCALE 5:1)



D1	4.35	0.171
E2	3.625	0.143
L2	0.68 REF	0.027 REF
	---	0° --- 10°

NOTE
1. PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
MOLD FLASH AT THE NON-LEAD SIDES

UNIT: mm

Disclaimer

Material Category Policy

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